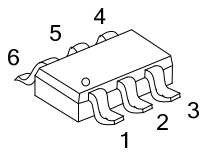
PUMT1

PNP SILICON TRANSISTOR

PNP GENERAL PURPOSE DUAL TRANSISTOR



SOT-363

■ DESCRIPTION

Two independently operating PNP transistors.

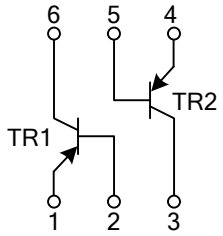
■ FEATURES

* Low Current (Max. -100mA)
* Low Voltage (Max. -40V)
* Reduces Number of Components and Board Space.
* Complement to PUMX1.

■ APPLICATIONS

*General Purpose Switching and Amplification.

■ EQUIVALENT CIRCUIT



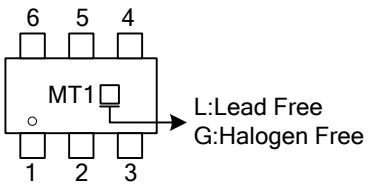
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment						Packing
Lead Free	Halogen Free		1	2	3	4	5	6	
PUMT1L-AL6-R	PUMT1G-AL6-R	SOT-363	E1	B1	C2	E2	B2	C1	Tape Reel

PUMT1L-AL6-R
(1)Packing Type
(2)Package Type
(3)Lead Free

(1) R: Tape Reel
(2) AL6: SOT-363
(3) G: Halogen Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current (DC)	I_C	-100	mA
Peak Collector Current	I_{CM}	-200	mA
Peak Base Current	I_{BM}	-200	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C)

PARAMETER	SYMBOL	CONDITION	MIN	TYP	MAX	UNIT
Collector Cut-Off Current	I_{CBO}	I_E=0, V_{CB}=-30V			-100	nA
		I_E=0, V_{CB}=-30V, T_J=150°C			-10	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-4V, I_C=0			-100	nA
DC Current Gain	h_{FE}	I_C=-1mA, V_{CE}=-6V	120			
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I_C=-50mA, I_B=-5mA (Note 1)			-200	mV
Collector Capacitance	Cc	I_E=I_E=0, V_{CB}=-12V, f=1MHz			2.2	pF
Transition Frequency	f_T	I_C=-2mA, V_{CE}=-12V, f=100MHz	100			MHz

Note: 1. Pulse test: Pulse Width≤300μs, Duty Cycle≤2.0%
2. The following characteristics apply to both TR1 and TR2.